

1M BIT (128K WORD x 8 BIT) CMOS MASK ROM
SILICON GATE CMOS

DESCRIPTION

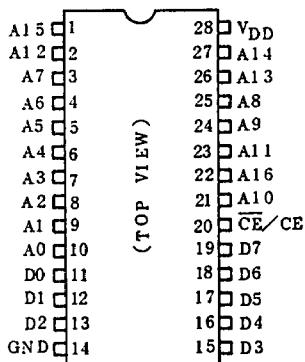
The TC531000CP/CF is a 1,048,576 bits read only memory organized as 131,072 words by 8 bits with a low bit cost, thus being suitable for use in program memory of microprocessor, especially character generator. The TC531000CP/CF using CMOS technology is most suitable for low power applications where battery operation are required. The TC531000CP/CF has one chip enable input CE/CE, programmable for device selection.

FEATURES

TC531000CP/CF	120ns Version	150ns Version
Access Time (max.)	120ns	150ns
Power Dissipation Operation Current (max.)	40mA	35mA
Power Dissipation Standby Current (max.)	20µA	20µA

- Single 5V Power Supply
- All Inputs and Outputs: TTL Compatible
- Three State Outputs
- Fully Static Operation
- Programmable Chip Enable
- Package
 - Plastic DIP: TC531000CP
 - Plastic FP : TC531000CF

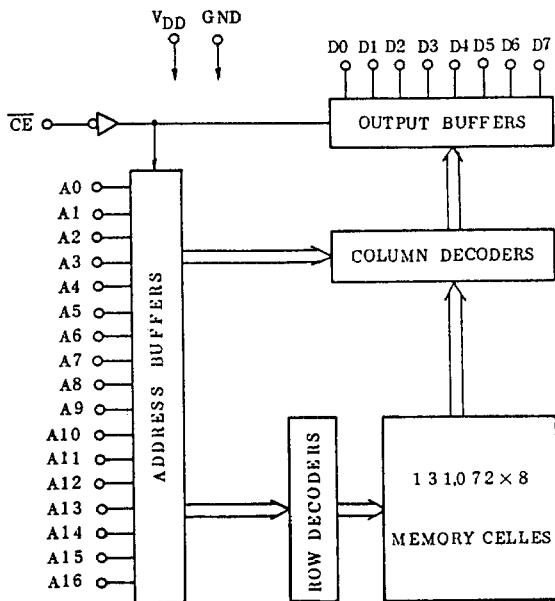
PIN CONNECTION



PIN NAMES

A0 ~ A16	Address Inputs
D0 ~ D7	Data Outputs
CE/CE	Chip Enable Input
V _{DD}	Power Supply
GND	Ground

BLOCK DIAGRAM



TC531000CP/CF-12/15

MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
V_{DD}	Power Supply Voltage	-0.5 ~ 7.0	V
V_{IN}	Input Voltage	-0.5 ~ V_{DD}	
V_{OUT}	Output Voltage	0 ~ V_{DD}	
P_D	Power Dissipation	1.0/0.6 *	W
T_{STG}	Storage Temperature	-55 ~ 150	
T_{OPR}	Operating Temperature	-40 ~ 70	$^{\circ}\text{C}$
T_{SOLDER}	Soldering Temperature • Time	260 • 10	

Note: * Plastic FP

DC OPERATING CONDITIONS ($T_a = -40 \sim 70^{\circ}\text{C}$)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V_{IH}	Input High Voltage	2.2	-	$V_{DD}+0.3$	
V_{IL}	Input Low Voltage	-0.3	-	0.8	

DC and OPERATING CHARACTERISTICS ($T_a = -40 \sim 70^{\circ}\text{C}$, $V_{DD} = 5\text{V} \pm 10\%$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{IL}	Input Leakage Current	$V_{IN}=0 \sim V_{DD}$	-	± 1.0	μA
I_{LO}	Output Leakage Current	$\bar{CE}=V_{IH}$, $V_{OUT}=0 \sim V_{DD}$	-	± 5.0	
I_{OH}	Output High Current	$V_{OH}=2.4\text{V}$	-1.0	-	mA
I_{OL}	Output Low Current	$V_{OL}=0.4\text{V}$	3.2	-	
I_{DDS1}	Standby Current	$CE=0.8\text{V}$ ($\bar{CE}=2.2\text{V}$)	-	2	μA
I_{DDS2}	Standby Current	$CE=0.2\text{V}$ ($\bar{CE}=V_{DD}-0.2\text{V}$)	-	20	
I_{DD01}	Operating Current	$V_{IN}=V_{IH}/V_{IL}$	$t_{cycle}=120\text{ns}$	-	50
		$I_{OUT}=0\text{mA}$	$t_{cycle}=150\text{ns}$	-	45
I_{DD02}		$V_{IN}=V_{DD}-0.2\text{V}/0.2\text{V}$	$t_{cycle}=120\text{ns}$	-	40
		$I_{OUT}=0\text{mA}$	$t_{cycle}=150\text{ns}$	-	35

CAPACITANCE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
C_{IN}	Input Capacitance	$f=1\text{MHz}$, $T_a=25^{\circ}\text{C}$	-	10	pF
C_{OUT}	Output Capacitance	$f=1\text{MHz}$, $T_a=25^{\circ}\text{C}$	-	10	

Note: This parameter is periodically sampled and is not 100% tested.

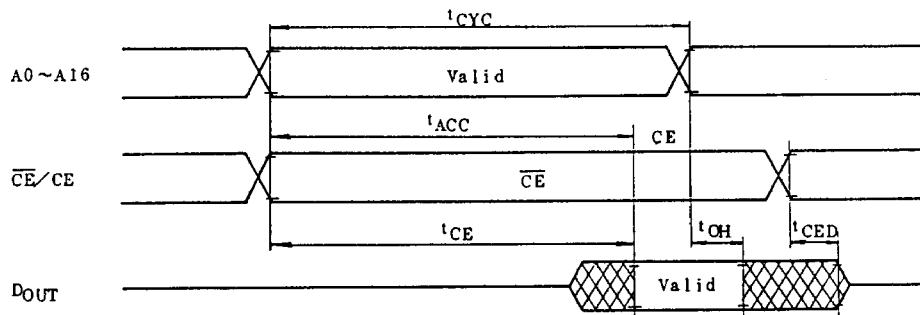
AC CHARACTERISTICS ($V_{DD}=5V\pm10\%$, $T_a=-40\sim70^\circ C$)

SYMBOL	PARAMETER	120ns Version		150ns Version		UNIT
		MIN.	MAX.	MIN.	MAX.	
t_{cycle}	Cycle Time	120	-	150	-	ns
t_{ACC}	Access Time	-	120	-	150	
t_{CE}	Chip Enable Access Time	-	120	-	150	
t_{CED}	Output Disable Time	-	50	-	50	
t_{OH}	Output Hold Time	5	-	5	-	

AC TEST CONDITION

- Output Load : $100\text{pF} + 1\text{TTL}$
- Input Levels : $0.6\text{V}, 2.4\text{V}$
- Timing Measurement Reference Levels
 Input : $0.8\text{V}, 2.2\text{V}$
 Output: $0.8\text{V}, 2.0\text{V}$
- Input Rise and Fall Time : 5ns

TIMING WAVEFORMS



OPERATING MODE

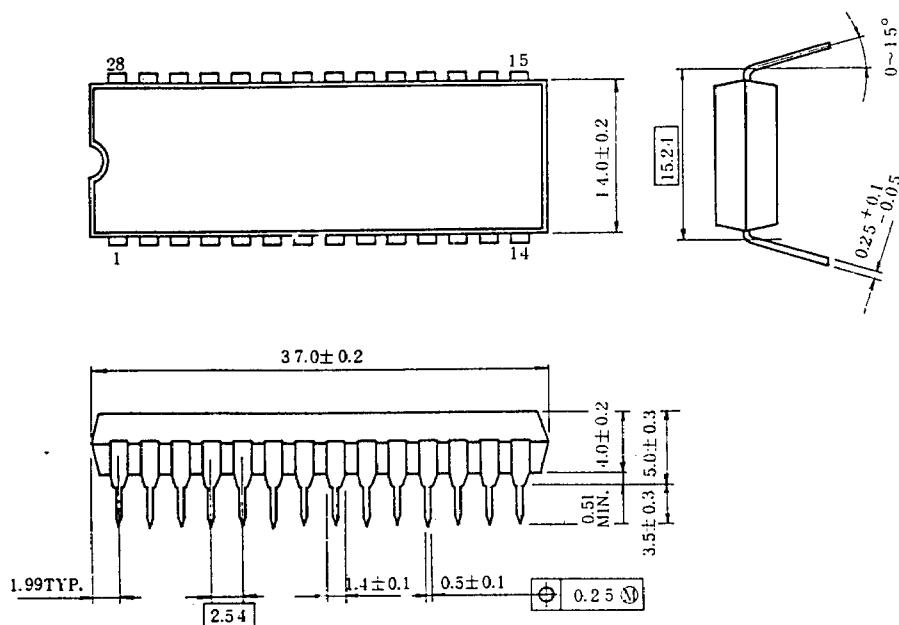
MODE	$\overline{CE}(CE)$	A0 ~ 16	Outputs	Power
Read	L(H)	Valid	Data Out	Operating
Standby	H(L)	*	High-Z	Standby

H: V_{IH} , L: V_{IL} , *: V_{IH} or V_{IL}

OUTLINE DRAWINGS

Plastic DIP (DIP28-P-600)

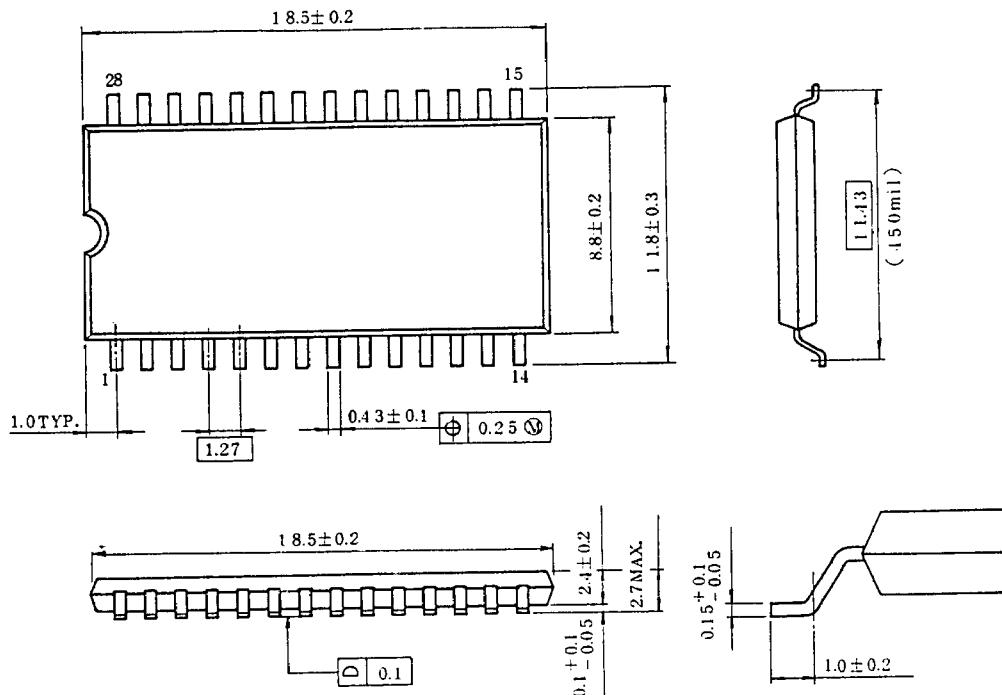
Unit in mm



Note: Package width and length do not include mold protrusion, allowable mold protrusion is 0.15mm.

Plastic FP (SOP28-P~450)

unit in mm



Note: Package width and length do not include mold protrusion, allowable mold protrusion is 0.15mm.